



ABSTRACT OF THE DISCLOSURE

When a semiconductor light emitting device or a semiconductor device is produced using a nitride type III-V group compound semiconductor substrate on which a plurality of second regions made of a crystal having a second average dislocation density are regularly arranged in a first region made of a crystal having a first average dislocation density so as to produce the structured substrate, the second average dislocation density being greater than the first average dislocation density, a light emitting region of the semiconductor light emitting device or an active region of the semiconductor device is formed in such a manner that it does not pass through any one of the second regions.